UNISONIC TECHNOLOGIES CO., LTD

MCR101 SCR

FH LW SENSITIVE GATE SILICON CONTROLLED RECTIFIERS REVERSE **BLOCKING THYRISTORS**

DESCRIPTION

PNPN devices designed for high volume, line-powered consumer applications such as relay and lamp drivers, small motor controls, gate drivers for larger thyristors, and sensing and detection circuits. Supplied in an inexpensive plastic TO-92 package which is readily adaptable for use in automatic insertion equipment.

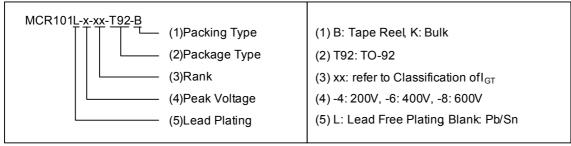
FEATURES

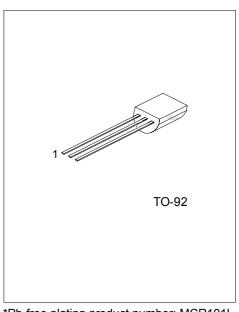
- *Sensitive gate allows triggering by micro controllers and other logic circuits
- *Blocking voltage to 600V
- *On-state current rating of 0.8A RMS at 80°C
- *High surge current capability 10A
- *Minimum and maximum values of IGT, VGT and IH specified for ease of design
- *Immunity to dV/dt 20V/µsec minimum at 110°C
- *Glass-passivated surface for reliability and uniformity

ORDERING INFORMATION

Order Number		Dookogo	Pin	Assign	Dooking				
Normal	Lead Free Plating	Package	1	2	3	Packing			
MCR101-x-xx-T92-B	MCR101L-x-xx-T92-B	TO-92	G	Α	С	Tape Box			
MCR101-x-xx-T92-K	MCR101L-x-xx-T92-K	TO-92	G	Α	С	Bulk			
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Note: Pin Assignment: G: Gate A: Anode C: Cathode





*Pb-free plating product number: MCR101L

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■ ABSOLUTE MAXIMUM RATINGS

PARAMETER	SYMBOL	RATINGS	UNIT	
Peak Repetitive Off-State Voltage(note) MCR10			200	
(T _J =-40 to 110°C, Sine Wave, 50 to 60Hz; Gate	MCR101-6	V_{DRM}, V_{RRM}	400	V
Open)	MCR101-8		600	
On-Sate RMS Current (Tc=80°C) 180° Condition Angles			0.8	Α
Peak Non-Repetitive Surge Current			10	۸
(1/2 cycle, Sine Wave, 60Hz, T _J =25°C)	I _{TSM}	10	Α	
Circuit Fusing Considerations (t=8.3 ms)	l ² t	0.415	A^2s	
Forward Peak Gate Power (T _A =25°C, Pulse Width	P_{GM}	0.1	W	
Forward Average Gate Power (T _A =25°C, t=8.3ms)	$P_{G(AV)}$	0.1	W	
Peak Gate Current – Forward (T _A =25°C, Pulse Wid	I _{GM}	1	Α	
Peak Gate Voltage – Reverse (T _A =25°C, Pulse Wid	V_{GRM}	5	V	
Operating Junction Temperature @ Rated V _{RRM} and	T_J	-40 ~ +110	°C	
Storage Temperature	T _{STG}	-40 ~ +150	°C	

Note: V_{DRM} and V_{RRM} for all types can be applied on a continuous basis. Ratings apply for zero or negative gate voltage; however, positive gate voltage shall not be applied concurrent with negative potential on the anode. Blocking voltages shall not be tested with a constant current source such that the voltage ratings of the devices are exceeded.

■ THERMAL DATA

PARAMETER	SYMBOL	RATING	UNIT
Thermal Resistance, Junction to Case	θ_{JC}	75	°C/W
Thermal Resistance, Junction to Ambient	θ_{JA}	200	°C/W

■ ELECTRICAL CHARACTERISTICS (T_J =25°C, unless otherwise stated)

PARAMETER		SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT	
OFF CHARACTERISTICS								
Peak Forward or Reverse	Tc=25°C	1	V D-t1V1V -D 41-0			10	^	
Blocking Current	Tc=125°C	IDRM, IRRM	V_D =Rated V_{DRM} and V_{RRM} ; R_{GK} =1k Ω			100	μΑ	
ON CHARACTERISTICS								
Peak Forward On-State Voltage	ge (Note1)	V_{TM}	I _{TM} =1A Peak @ T _A =25°C			1.7	V	
Gate Trigger Current (Continuous dc)(note2)		I _{GT}	V _{AK} =7Vdc, R _L =100Ω, T _C =25°C		40	200	μΑ	
Holding Current (note 2)	Tc=25 °C	- I _H	\/ -7\/da initiating augus at 20m A		0.5	5	ν Λ	
Holding Current (note 3)	Tc=-40 °C		V _{AK} =7Vdc, initiating current=20mA			10	mA	
Latch Current	Tc=25°C		\/ =7\/ a=200\		0.6	10	س ۸	
Laten Current	Tc=-40 °C	ال	V _{AK} =7V, Ig=200μA			15	mA	
Gate Trigger Current	Tc=25 °C	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	V_{AK} =7Vdc, R_L =100 Ω		0.62	0.8	\	
(continuous dc) (Note 2)	Tc=-40 °C	V_{GT}				1.2	V	
DYNAMIC CHARACTERISTICS								
Critical Rate of Rise of Off-State Voltage dV/d		dV/dt	V _D =Rated V _{DRM} , Exponential Waveform, R _{GK} =1000Ω, T _J =110°C	20	35		V/μs	
Critical Rate of Rise of On-State Current di/dt		I _{PK} =20A, Pw=10μsec diG/dt=1A/μsec, Iqt=20mA			50	A/μs		

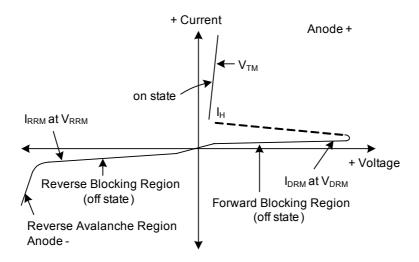
Notes: 1. Indicates Pulse Test Width≤1.0ms, duty cycle ≤1%

- 2. $R_{\text{GK}}\text{=}1000\Omega$ included in measurement.
- 3. Does not include R_{GK} in measurement.

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■ VOLTAGE CURRENT CHARACTERISTIC OF SCR

SYMBOL	PARAMETER	
V_{DRM}	Peak Repetitive Off Stat Forward Voltage	
I _{DRM}	Peak Forward Blocking Current	
V_{RRM}	Peak Repetitive Off State Reverse Voltage	
I_{RRM}	Peak Reverse Blocking Current	
V _{TM} Peak On State Voltage		
I _H Holding Current		



■ CLASSIFICATION OF I_{GT}

RANK	В	С	AA	AB	AC	AD	
RANGE	48~105μA	95~200μΑ	8~16μA	14~21μA	19~25μA	23~52μA	

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■ TYPICAL CHARACTERISTICS

Figure 1. Typical Gate Trigger Current versus Junction Temperature

100
90
80
70
60
40
20
10
-40 -25 -10 5 20 25 50 65 80 95 110
Junction Temperature, T_J()

Figure 2. Typical Gate Trigger Voltage versus Junction Temperature

1.0

90.9

0.8

0.7

0.6

0.5

0.7

0.7

0.8

0.9

0.9

0.9

0.1

0.3

0.2

-40 -25 -10 5 20 25 50 65 80 95 110

Junction Temperature, T_J ()

Figure 3. Typical Holding Current versus Junction Temperature

1000

(Y 1)

100

100

-40 -25 -10 5 20 25 50 65 80 95 110

Junction Temperature, T_J()

Figure 4. Typical Latching Current versus Junction Temperature

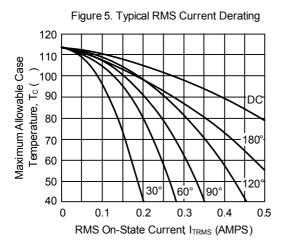
1000

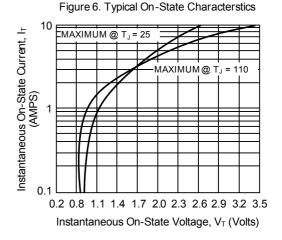
(Y 1)

100

40 -25 -10 5 20 25 50 65 80 95 110

Junction Temperature, T_J ()





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